# Voltage Regulator -Low Dropout

# 400 mA

# NCV4274C

### Description

The NCV4274C is a precision micro-power voltage regulator with an output current capability of 400 mA available in the DPAK, D2PAK and SOT-223 packages.

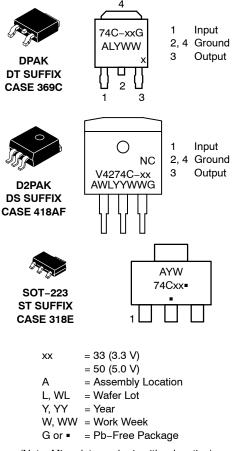
The output voltage is accurate within  $\pm 2.0\%$  with a maximum dropout voltage of 0.5 V with an input up to 40 V. Low quiescent current is a feature drawing only 125  $\mu$ A with a 1 mA load. This part is ideal for automotive and all battery operated microprocessor equipment.

The regulator is protected against reverse battery, short circuit, and thermal overload conditions. The device can withstand load dump transients making it suitable for use in automotive environments.

## Features

- 3.3 V, 5.0 V, ±2.0% Output Options
- Low 125 µA Quiescent Current at 1 mA load current
- 400 mA Output Current Capability
- Fault Protection
- +60 V Peak Transient Voltage with Respect to GND
  - -42 V Reverse Voltage
  - Short Circuit
  - Thermal Overload
- Very Low Dropout Voltage
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

### MARKING DIAGRAMS



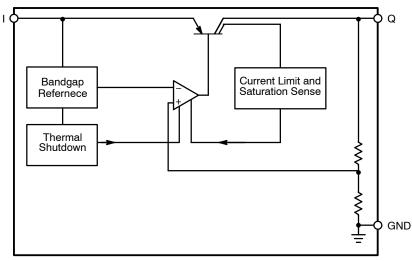
(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 12 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 12.

1





#### **Pin Definitions and Functions**

Pin No.	Symbol	Function
1	I	Input; Bypass directly at the IC with a ceramic capacitor to GND.
2,4	GND	Ground
3	Q	Output; Bypass with a capacitor to GND.

### **ABSOLUTE MAXIMUM RATINGS**

Pin Symbol, Parameter	Pin Symbol, Parameter			Min	Max	Unit
I, Input-to-Regulator	Voltage	VI		-42	45	V
	Current	I <sub>I</sub>		Internally Limited	Internally Limited	
I, Input peak Transient Voltage to Regulator with Respect to GND (Note 1)		VI			60	V
<b>Q</b> , Regulated Output	Voltage	VQ	$V_Q = V_I$	-1.0	40	V
	Current	Ι <sub>Q</sub>		Internally Limited	Internally Limited	
GND, Ground Current		I <sub>GND</sub>		-	100	mA
Junction Temperature Storage Temperature		T <sub>J</sub> T <sub>Stg</sub>		-40 -50	150 150	°C °C
ESD Capability, Human Body Model (Note 2)		ESD <sub>HB</sub>		4		kV
ESD Capability, Machine Model (Note 2)		ESD <sub>MM</sub>		200		V
ESD Capability, Charged Device Model (Note	2)	ESD <sub>CDM</sub>		1		kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Load Dump Test B (with centralized load dump suppression) according to ISO16750-2 standard. Guaranteed by design. Not tested in production. Passed Class C. This device series incorporates ESD protection and is tested by the following methods:

2.

ESD HBM tested per AEC-Q100-002 (EIA/JESD22-A114)

ESD MM tested per AEC-Q100-003 (EIA/JESD22-A115)

Field Induced Charge Device Model ESD characterization is not performed on plastic molded packages with body sizes <50mm<sup>2</sup> due to the inability of a small package body to acquire and retain enough charge to meet the minimum CDM discharge current waveform characteristic defined in JEDEC JS-002-2014.

## **OPERATING RANGE**

Parameter	Symbol	Condition	Min	Max	Unit
Input Voltage (5.0 V Version)	VI		5.5	40	V
Input Voltage (3.3 V Version)	VI		4.5	40	V
Junction Temperature	TJ		-40	150	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### THERMAL RESISTANCE

Parameter		Symbol	Condition	Min	Мах	Unit
Junction-to-Ambient	DPAK	R <sub>thja</sub>		-	72.5 (Note 3)	°C/W
Junction-to-Ambient	D2PAK	R <sub>thja</sub>		-	56.7 (Note 3)	°C/W
Junction-to-Case	DPAK	R <sub>thjc</sub>		-	5.8	°C/W
Junction-to-Case	D2PAK	R <sub>thjc</sub>		-	5.8	°C/W
Junction-to-Tab	SOT-223	$\Psi_{-JLX},\ \Psi_{LX}$		-	15.6 (Note 3)	°C/W
Junction-to-Ambient	SOT-223	$R_{\theta JA}, \theta_{JA}$		-	87 (Note 3)	°C/W

3. 1 oz copper, 300 mm<sup>2</sup> copper area, single-sided FR4 PCB.

## MOISTURE SENSITIVITY LEVEL (Note 4)

Parameter	Symbol	Condition	Min	Мах	Unit
Moisture Sensitivity Level	MSL	DPAK and D2PAK SOT-223	1 3	-	

4. For more information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **ELECTRICAL CHARACTERISTICS**

 $-40^\circ C < T_J < 150^\circ C; \, V_I$  = 13.5 V unless otherwise noted.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
REGULATOR	-		-	-	-	-
Output Voltage (5.0 V Version)	V <sub>Q</sub>	5 mA < I <sub>Q</sub> < 400 mA 6 V < V <sub>I</sub> < 28 V	4.9	5.0	5.1	V
Output Voltage (5.0 V Version)	V <sub>Q</sub>	5 mA < I <sub>Q</sub> < 200 mA 6 V < V <sub>I</sub> < 40 V	4.9	5.0	5.1	V
Output Voltage (3.3 V Version)	V <sub>Q</sub>	5 mA < I <sub>Q</sub> < 400 mA 4.5 V < V <sub>I</sub> < 28 V	3.23	3.3	3.37	V
Output Voltage (3.3 V Version)	V <sub>Q</sub>	5 mA < I <sub>Q</sub> < 200 mA 4.5 V < V <sub>I</sub> < 40 V	3.23	3.3	3.37	V
Current Limit (All Versions)	ا <sub>Q</sub>	V <sub>Q</sub> = 90% V <sub>QTYP</sub>	400	600	-	mA
Quiescent Current	l <sub>q</sub>	$ \begin{split} I_Q &= 1 \text{ mA} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 3.3 \text{ V} \\ I_Q &= 250 \text{ mA} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 3.3 \text{ V} \\ I_Q &= 400 \text{ mA} \\ V_Q &= 5.0 \text{ V} \\ V_Q &= 3.3 \text{ V} \end{split} $		125 125 5 5 10 10	250 250 15 15 35 35	μΑ μΑ mA mA mA
Dropout Voltage 5.0 V Version	V <sub>DR</sub>	$I_Q = 250 \text{ mA},$ $V_{DR} = V_I - V_Q$ $V_I = 5.0 \text{ V}$	-	250	500	mV
Load Regulation (3.3 V and 5 V Versions)	$\Delta V_Q$	I <sub>Q</sub> = 5 mA to 400 mA	-	3	20	mV
Line Regulation (3.3 V and 5 V Versions)	ΔVQ	$\Delta V_{I} = 12 \text{ V to } 32 \text{ V}$ I <sub>Q</sub> = 5 mA	-	4	25	mV
Power Supply Ripple Rejection	PSRR	fr = 100 Hz, V <sub>r</sub> = 0.5 V <sub>PP</sub>	-	60	-	dB
Thermal Shutdown Temperature*	T <sub>SD</sub>	I <sub>Q</sub> = 5 mA	150	-	210	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. \*Guaranteed by design, not tested in production

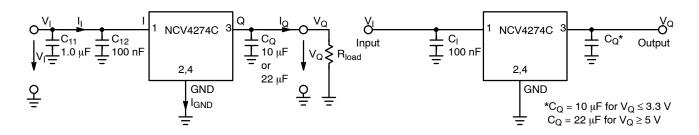
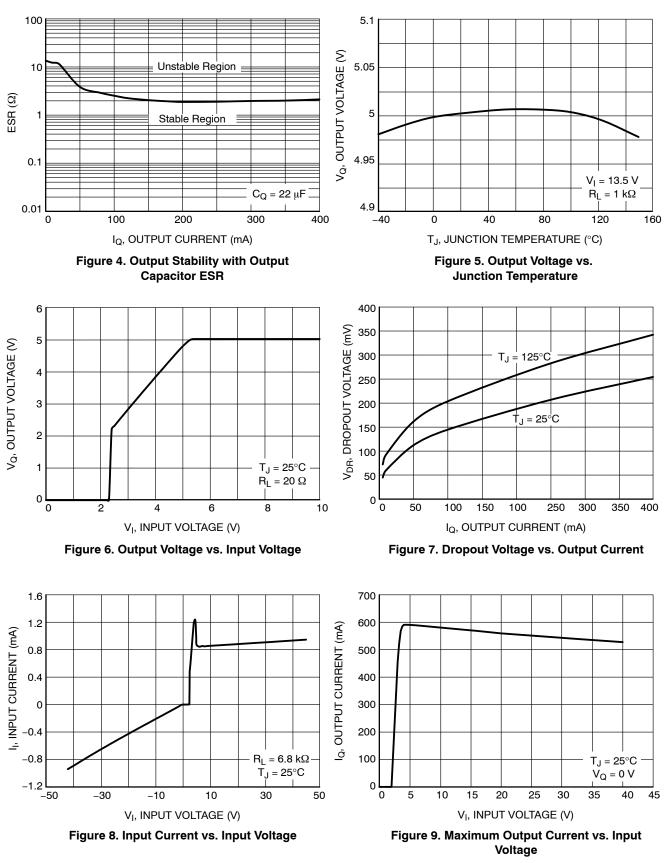


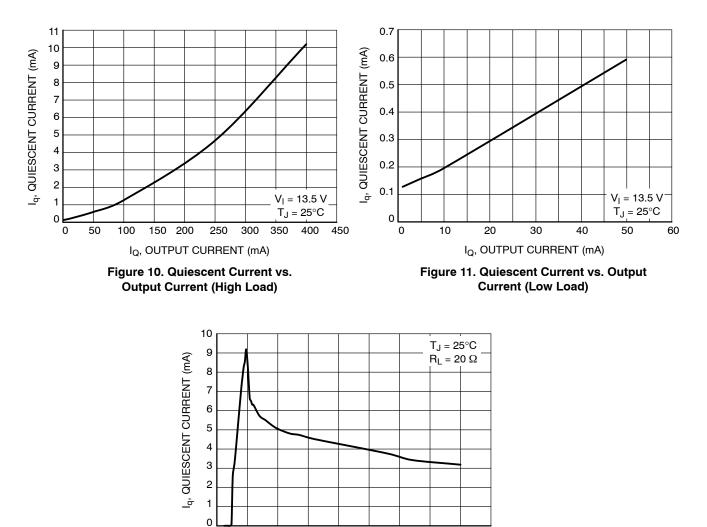
Figure 2. Measuring Circuit

Figure 3. Application Circuit



#### **TYPICAL CHARACTERISTIC CURVES - 5 V VERSION**

# **TYPICAL CHARACTERISTIC CURVES – 5 V VERSION**



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35 40

45

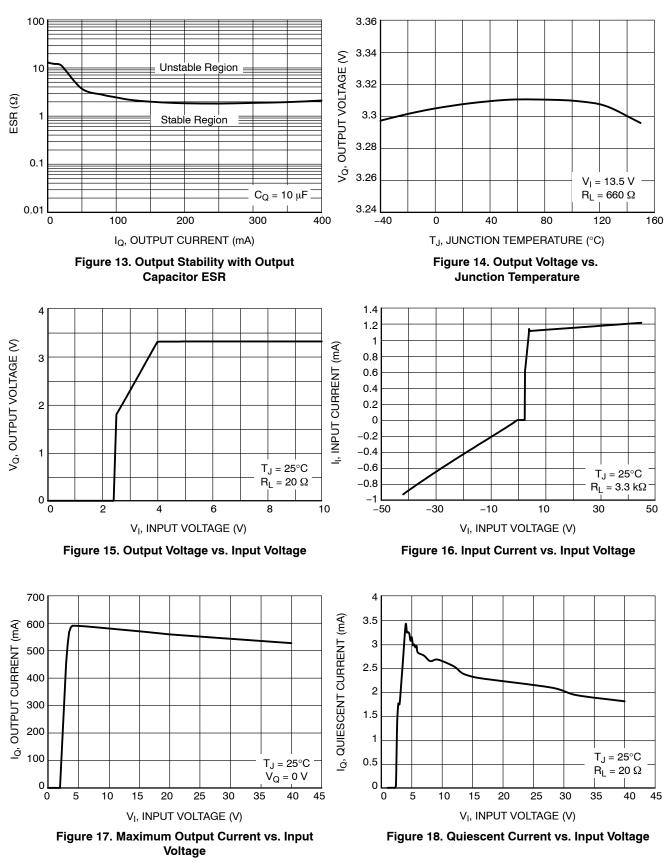
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V<sub>I</sub>, INPUT VOLTAGE (V) Figure 12. Quiescent Current vs. Input Voltage

5

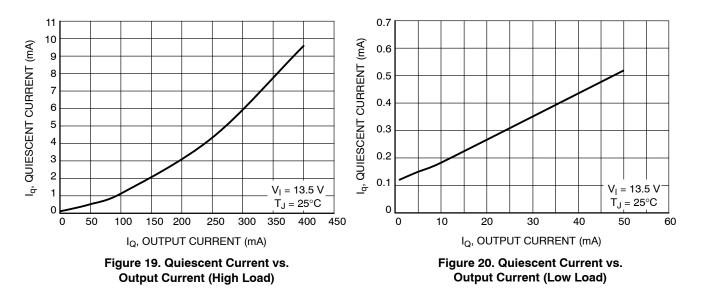
10 15

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**TYPICAL CHARACTERISTIC CURVES - 3.3 V VERSION** 

# **TYPICAL CHARACTERISTIC CURVES – 3.3 V VERSION**



#### **APPLICATION DESCRIPTION**

#### **Output Regulator**

The output is controlled by a precision trimmed reference and error amplifier. The PNP output has saturation control for regulation while the input voltage is low, preventing over saturation. Current limit and voltage monitors complement the regulator design to give safe operating signals to the processor and control circuits.

#### **Stability Considerations**

The input capacitor  $C_{I1}$  in Figure 2 is necessary for compensating input line reactance. Possible oscillations caused by input inductance and input capacitance can be damped by using a resistor of approximately 1  $\Omega$  in series with  $C_{I2}$ .

The output or compensation capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability.

The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive solution, but, if the circuit operates at low temperatures  $(-25^{\circ}C \text{ to } -40^{\circ}C)$ , both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The value for the output capacitor  $C_Q$  shown in Figure 2 should work for most applications; however, it is not necessarily the optimized solution. Actual Stability Regions are shown in a graphs in the Typical Performance Characteristics section.

# Calculating Power Dissipation in a Single Output Linear Regulator

The maximum power dissipation for a single output regulator (Figure 3) is:

$$P_{D(max)} = [V_{I(max)} - V_{Q(min)}]I_{Q(max)} + V_{I(max)}I_{q}$$
 (eq. 1)

Where:

 $V_{I(max)}$  is the maximum input voltage,

 $V_{Q(min)}$  is the minimum output voltage,

 $I_{Q\left(max\right)}$  is the maximum output current for the application, and

 $I_q$  is the quiescent current the regulator consumes at  $I_{Q(max)}$ .

Once the value of  $P_{D(max)}$  is known, the maximum permissible value of  $R_{0JA}$  can be calculated:

$$\mathsf{P}_{\theta_{\mathsf{JA}}} = \frac{(150 \text{ C} - \mathsf{T}_{\mathsf{A}})}{\mathsf{P}_{\mathsf{D}}} \tag{eq. 2}$$

The value of  $R_{\theta JA}$  can then be compared with those in the package section of the data sheet. Those packages with  $R_{\theta JA}$ 's less than the calculated value in Equation 2 will keep the die temperature below 150°C. In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heat sink will be required. The current flow and voltages are shown in the Measurement Circuit Diagram.

#### **Heat Sinks**

A heat sink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of  $R_{\theta JA}$ :

$$\mathbf{R}_{\theta \mathsf{JA}} = \mathbf{R}_{\theta \mathsf{JC}} + \mathbf{R}_{\theta \mathsf{CS}} + \mathbf{R}_{\theta \mathsf{SA}} \tag{eq. 3}$$

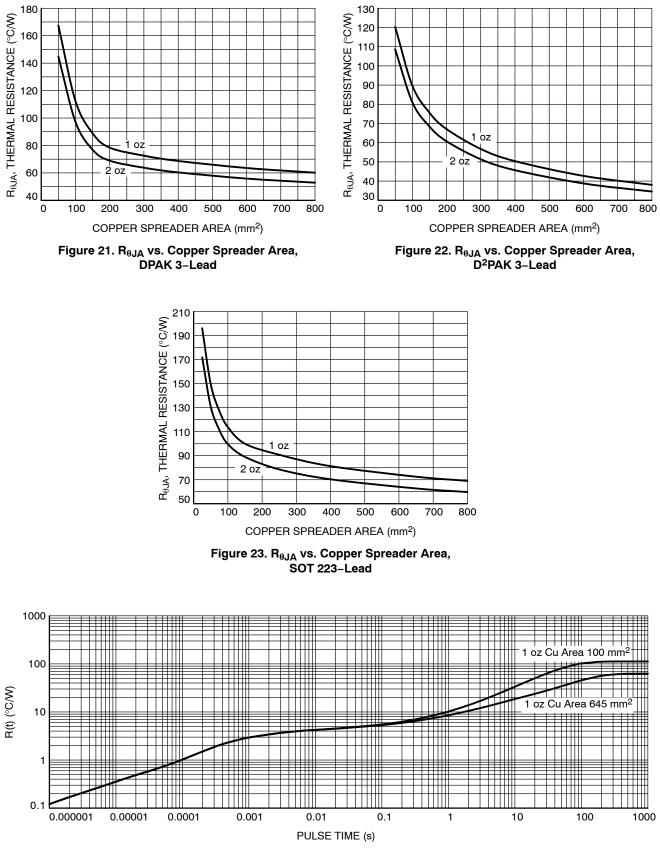
Where:

 $R_{\theta JC}$  = the junction-to-case thermal resistance,

 $R_{\theta CS}$  = the case-to-heat sink thermal resistance, and  $R_{\theta SA}$  = the heat sink-to-ambient thermal resistance.

 $R_{\theta JC}$  appears in the package section of the data sheet. Like  $R_{\theta JA}$ , it too is a function of package type.  $R_{\theta CS}$  and  $R_{\theta SA}$  are functions of the package type, heat sink and the interface between them. These values appear in data sheets of heat sink manufacturers.

Thermal, mounting, and heat sinking are discussed in the **onsemi** application note AN1040/D, available on the **onsemi** Website.





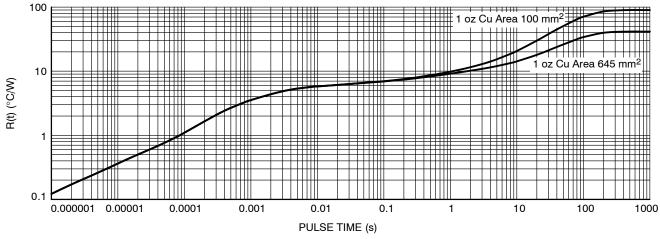
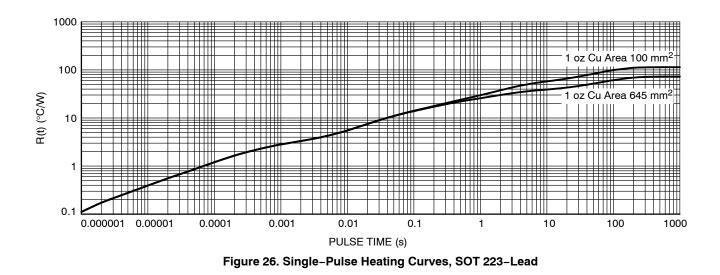


Figure 25. Single-Pulse Heating Curves, D<sup>2</sup>PAK 3-Lead



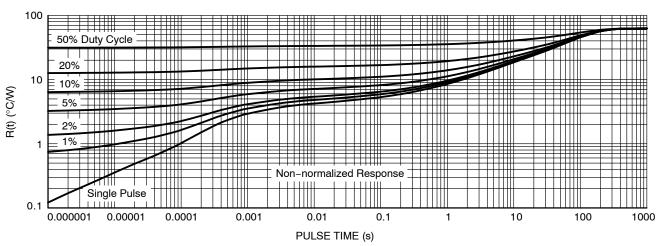


Figure 27. Duty Cycle for 1 inch<sup>2</sup> (645 mm<sup>2</sup>) Spreader Board, DPAK 3-Lead

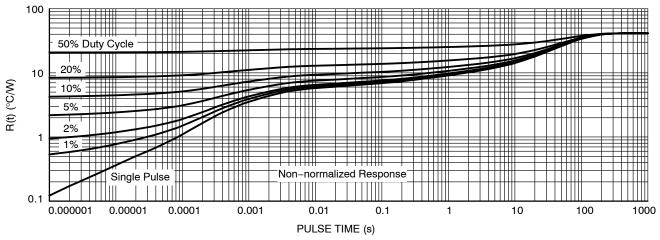


Figure 28. Duty Cycle for 1 inch<sup>2</sup> (645 mm<sup>2</sup>) Spreader Board, D<sup>2</sup>PAK 3-Lead

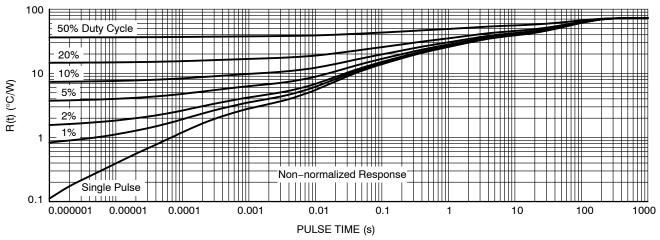


Figure 29. Duty Cycle for 1 inch<sup>2</sup> (645 mm<sup>2</sup>) Spreader Board, SOT 223-Lead

### **ORDERING INFORMATION**

Device*	Output Voltage Accu- racy	Output Voltage	Package	Shipping <sup>†</sup>
NCV4274CDT33RKG	2%	3.3 V	DPAK (Pb-Free)	2500 / Tape & Reel
NCV4274CDT50RKG	2%	5.0 V	DPAK (Pb-Free)	2500 / Tape & Reel
NCV4274CST33T3G	2%	3.3 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274CST50T3G	2%	5.0 V	SOT-223 (Pb-Free)	4000 / Tape & Reel

#### **DISCONTINUED** (Note 5)

NCV4274CDS33R4G	2%	3.3 V	D2PAK (Pb-Free)	800 / Tape & Reel
NCV4274CDS50R4G	2%	5.0 V	D2PAK (Pb-Free)	800 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

5. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on <u>www.onsemi.com</u>.



SOT-223 (TO-261) CASE 318E-04 ISSUE R

SEE DETAIL A

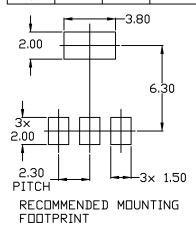
FRONT VIEW

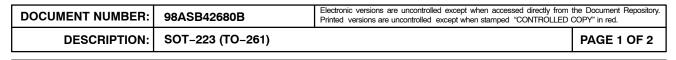
DATE 02 OCT 2018



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- AI IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS & AND &1.

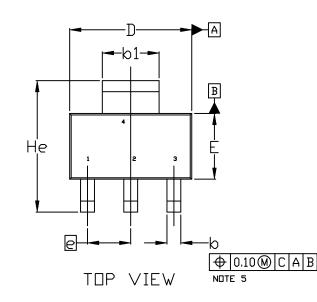
	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
A	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
b	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
с	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
e	i	5.30 B2C	;	
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0*		10*	

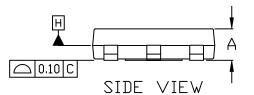


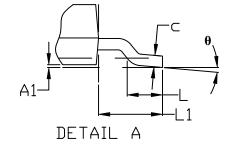


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SCALE 1:1







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#### SOT-223 (TO-261) CASE 318E-04 **ISSUE R**

#### DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	Style 12: Pin 1. Input 2. Output 3. NC 4. Output	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

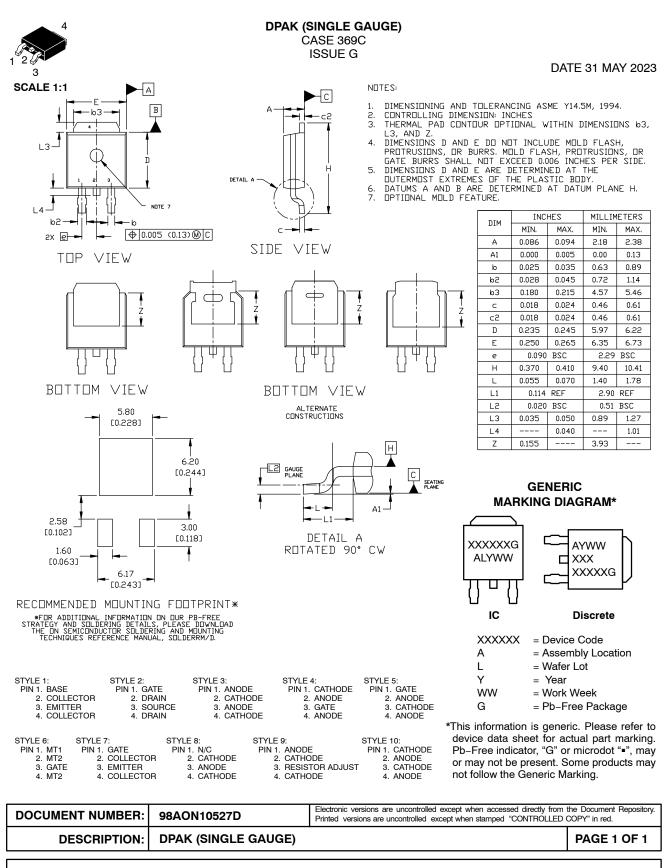
# GENERIC **MARKING DIAGRAM\***



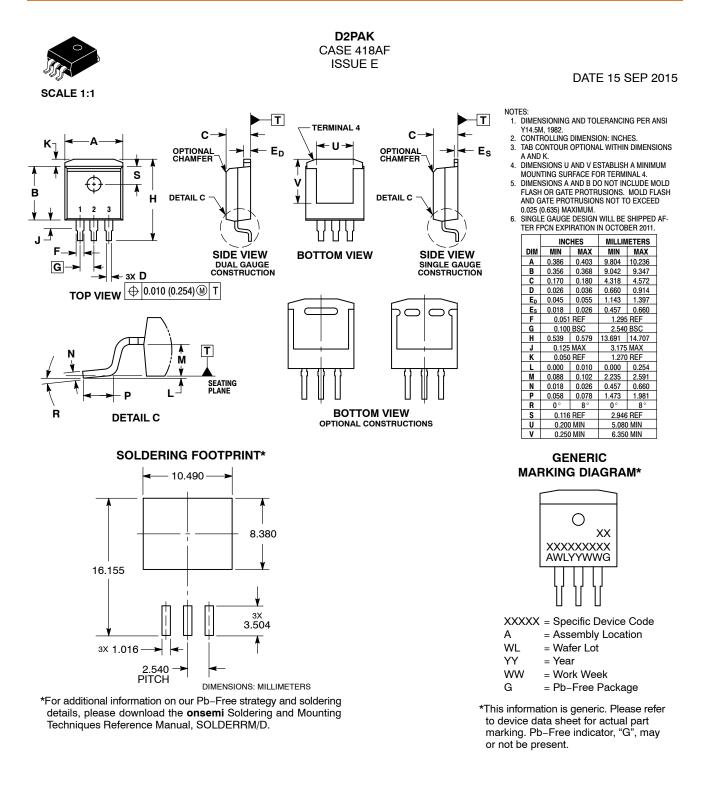
- = Assembly Location А
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code .
- = Pb-Free Package
- (Note: Microdot may be in either location) \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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